IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

JUL 1 8 2005 (1) Applicant:

Leonard Forbes

Examiner:

Joannie A. Garcia

Serial No.:

10/634,174

Group Art Unit:

2823 1303.102US1

Filed: Title: August 05, 2003 Docket:

STRAINED Si/SiGe/SOI ISLANDS AND PROCESSES OF MAKING SAME

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

MS Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 et. seq., the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicant respectfully requests that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicant requests that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicant with the next official communication.

Pursuant to 37 C.F.R. §1.97(c)(2), Applicants have included the fee of \$180.00 as set forth in 37 C.F.R. §1.17(p). Please charge any additional fees or credit any overpayment to Deposit Account No. 19-0743.

07/19/2005 WABDELRI 00000073 10634174

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Serial No :10/634,174

Filing Date: August 05, 2003

Title: STRAINED Si/SiGe/SOI ISLANDS AND PROCESSES OF MAKING SAME

Page 2 Dkt: 1303.102US1

The Examiner is invited to contact the Applicant's Representative at the below-listed telephone number if there are any questions regarding this communication.

Pursuant to 37 C.F.R. 1.98(a)(2), Applicant believes that copies of cited U.S. Patents and Published Applications are no longer required to be provided to the Office. Notification of this change was provided in the United States Patent and Trademark Office OG Notices dated October 12, 2004. Thus, Applicant has not included copies of any US Patents or Published Applications cited with this submission. Should the Office require copies to be provided, Applicant respectfully requests that notice of such requirement be directed to Applicant's below-signed representative. Applicant acknowledges the requirement to submit copies of foreign patent documents and non-patent literature in accordance with 37 C.F.R. 1.98(a)(2).

Respectfully submitted,

LEONARD FORBES

By his Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A. P.O. Box 2938
Minneapolis, MN 55402

(612) 373-6960

Date 7-13-05

Marvin L. Beekman

Reg. No. 38,377

N----

Signature Lee

PTO/SB/08A(10-01)
Approved for use through 10/31/2002, OMB 651-0031
US Patent & Trademark Office: U.S. DEPARTMENT OF COMMERCE

Substitute for form 1449A/PTO Complete if Known INFORMATION DISCLOSURE **Application Number** 10/634,174 STATEMENT BY APPEICAN (Use as many sheets as negessary) Filing Date August 5, 2003 Forbes, Leonard **First Named Inventor Group Art Unit** 2823 Garcia, Joannie **Examiner Name** Attorney Docket No: 1303.102US1 Sheet 1 of 1

US PATENT DOCUMENTS				
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate
	US-4,962,051	10/09/1990	Liaw, H. M.	11/18/1988
	US-5,735,949	04/07/1998	Mantl, S., et al.	09/13/1991
	US-6,825,102	11/30/2004	Bedell, S. W., et al.	09/18/2003

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	T ²		

	OTHE	R DOCUMENTS NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item No 1 (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		
		KAL, S., et al., "Strained Silicon-SiGe Devices Using Germanium Implantation", IETE Journal of Research, 43 (2-3), (Mar. 1997), 185-192	
		XIAO, Q., et al., "Preparation of thin Strained Si Film by Low Temperature Ge lon Implantation and High Temperature Annealing", Solid-State and Integrated Circuits Technology, 2004. Proceedings 7th Int'l Conf., 3(3), (Oct. 18, 2004), 2163-2166	

PTO/SB/08A(10-01)
Approved for use through 10/31/2002. OMB 651-0031
US Patent & Trademark Office: U.S. DEPARTMENT OF COMMERCE

Substitute for form 1449A/PTO
INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(Use as many sheets as necessary)



Application Number	10/634,174
Filing Date	August 5, 2003
First Named Inventor	Forbes, Leonard
Group Art Unit	2823
Examiner Name	Garcia, Joannie

Sheet 1 of 1

Attorney Docket No: 1303.102US1

Examiner	L UCD D	US PATE	ENT DOCUMENTS	•
Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate
	US-2004/0171196-A1	09/02/2004	Walitzki, H J.	08/07/2003
	US-2004/0173798	09/09/2004	Forbes, Leonard	03/05/2003
	US-2004/0214366-A1	10/28/2004	Segal, B M., et al.	05/20/2004
	US-2004/0217352-A1	11/04/2004	Forbes, L.	04/29/2003
	US-2004/0217391	11/04/2004	Forbes, Leonard	04/29/2003
	US-2004/0224480-A1	11/11/2004	Forbes, L.	05/07/2003
	US-2004/0232422-A1	11/25/2004	Forbes, L.	05/21/2003
	US-2004/0232487-A1	11/25/2004	Forbes, L.	05/21/2003
	US-2004/0232488-A1	11/25/2004	Forbes, L.	05/21/2003
	US-2004/0235264-A1	11/25/2004	Forbes, L.	05/21/2003
	US-2005/0017273-A1	01/27/2005	Forbes, L., et al.	07/21/2003
	US-2005/0020094-A1	01/27/2005	Forbes, L., et al.	07/21/2003
	US-2005/0023529-A1	02/03/2005	Forbes, L.	08/31/2005
	US-2005/0023612-A1	02/03/2005	Forbes, L.	08/31/2004
	US-2005/0023616-A1	02/03/2005	Forbes, L.	08/31/2004
	US-2005/0029683-A1	02/10/2005	Forbes, L., et al.	08/31/2004
	US-2005/0032296-A1	02/10/2005	Forbes, L.	08/31/2004
	US-4,523,975	06/18/1985	Groves, C. K., et al.	04/28/1982
	US-5,854,501	12/29/1998	Kao, D. Y.	11/20/1995
	US-5,877,070	03/02/1999	Goesele, U. M., et al.	05/31/1997
	US-5,987,200	11/16/1999	Fleming, D. A., et al.	10/27/1997
	US-6,103,598	08/15/2000	Yamagata, K., et al.	07/11/1996
	US-6,143,628	11/07/2000	Sato, N., et al.	03/25/1998
	US-6,162,657	12/19/2000	Schiele, I., et al.	05/11/1999
	US-6,180,487	01/30/2001	Lin, M.	10/25/1999
	US-6,328,796	12/11/2001	Kub, F. J., et al.	02/01/1999
	US-6,455,397	09/24/2002	Belford, Rona E.	11/09/2000
	US-6,486,008	11/26/2002	Lee, T.	08/01/2000
	US-6,497,763	12/24/2002	Kub, F. J., et al.	01/19/2001
	US-6,514,836	02/04/2003	Belford, Rona E.	06/04/2001
	US-6,656,822	12/02/2003	Doyle, B. S., et al.	06/28/1999
	US-6,689,671	02/10/2004	Yu, B, et al.	05/22/2002
	US-6,812,508	11/02/2004	Fukumi, M.	11/27/2001

	OTHE	R DOCUMENTS NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	No 1	(book, magazine, Journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
		LU, X., et al., "SiGe and SiGeC Surface Alloy Formation Using High-Dose Implantation and Solid Phase Epitaxy", <u>Proceedings of the 11th International Conference on Ion Implantation Technology</u> , Austin, TX, (1997), 686-689	

EXAMINER

DATE CONSIDERED